DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

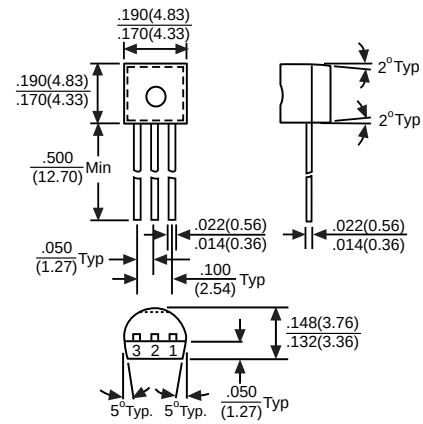
2SB564A

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

Designed for low frequency power amplifier applications.

TO-92



Dimensions in inches and (millimeters)

Pinning

1 = Emitter
2 = Collector
3 = Base

Absolute Maximum Ratings(T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1	A
Total Power Dissipation	P_D	800	mW
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55 to +150	°C

Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Volatge	BV_{CBO}	-30	-	-	V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-25	-	-	V	I_C=-10mA, I_B=0
Emitter-Base Breakdown Volatge	BV_{EBO}	-5	-	-	V	I_E=-100μA, I_C=0
Collector Cutoff Current	I_{CBO}	-	-	-100	nA	V_{CB}=-30V, I_E=0
Collector-Emitter Saturation Voltage(1)	$V_{CE(sat)}$	-	-	-0.5	V	I_C=-1A, I_B=-100mA
Base-Emitter Saturation Voltage(1)	$V_{BE(sat)}$	-	-	-1.2	V	I_C=-1A, I_B=-100mA
DC Current Gain(1)	h_{FE}	70	-	400	-	I_C=-100mA, V_{CE}=-1V
Transition Frequency	f_T	-	110	-	MHz	I_C=-10mA, V_{CE}=-6V, f=100MHz
Output Capacitance	C_{ob}	-	18	-	pF	V_{CB}=-6V, f=1MHz

(1)Pulse Test: Pulse Width ≦380μs, Duty Cycle ≦2%

Classification of h_{FE}

Rank	O	Y	GR
Range	70~140	120~240	200~400